

描述 / Descriptions

SOT-23 塑封封装 PNP 半导体三极管。Silicon PNP transistor in a SOT-23 Plastic Package.

特征 / Features

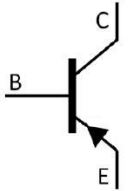
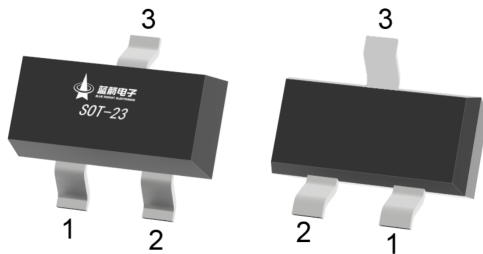
集电极电流可达 500mA，符合 AEC-Q101 标准高可靠性要求，无卤产品。

Collector currents up to 500 mA, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

用途 / Applications

用于普通放大及开关电路，满足汽车应用的严格要求。

General purpose amplifier and switch requiring, Meet the stringent requirements of automotive applications.

内部等效电路 / Equivalent Circuit**引脚排列 / Pinning**

PIN 1 : Base

PIN 2 : Emitter

PIN 3 : Collector

放大及印章代码 / h_{FE} Classifications & Marking

h _{FE} Range	100~300
Marking	2TQ

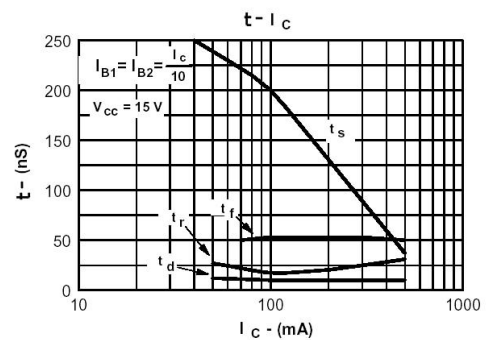
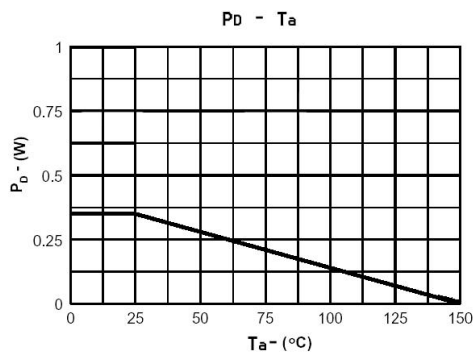
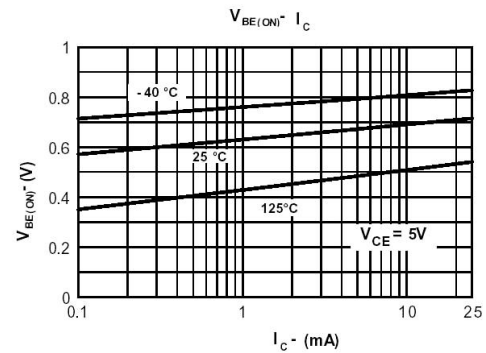
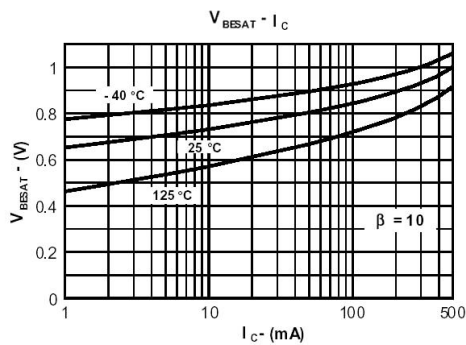
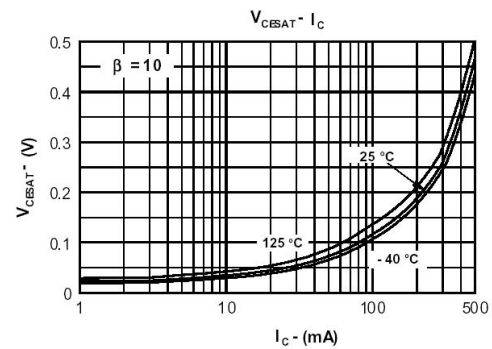
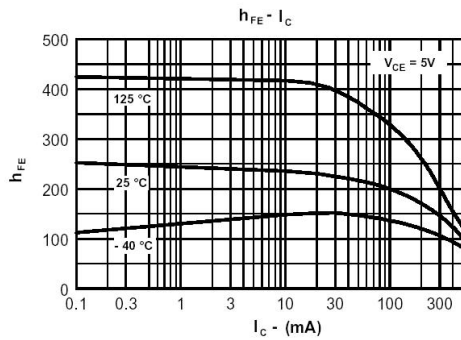
极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-40	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-600	mA
Collector Power Dissipation	P_C	350	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C = -0.1mA$ $I_E = 0$	-40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -1.0mA$ $I_B = 0$	-40			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E = -0.1mA$ $I_C = 0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -40V$ $I_E = 0$			-50	nA
Emitter Cut-Off Current	I_{EBO}	$V_{EB} = -5.0V$ $I_C = 0$			-50	nA
DC Current Gain	$h_{FE(1)}$	$V_{CE} = -2.0V$ $I_C = -150mA$	100		300	
	$h_{FE(2)}$	$V_{CE} = -1.0V$ $I_C = -0.1mA$	30			
	$h_{FE(3)}$	$V_{CE} = -1.0V$ $I_C = -1.0mA$	60			
	$h_{FE(4)}$	$V_{CE} = -1.0V$ $I_C = -10mA$	100			
	$h_{FE(5)}$	$V_{CE} = -2.0V$ $I_C = -500mA$	20			
Collector-Emitter Saturation voltage	$V_{CE(sat)(1)}$	$I_C = -150mA$ $I_B = -15mA$			-0.4	V
	$V_{CE(sat)(2)}$	$I_C = -500mA$ $I_B = -50mA$			-0.75	V
Base-Emitter Saturation Voltage	$V_{BE(sat)(1)}$	$I_C = -150mA$ $I_B = -15mA$	-0.75		-0.95	V
	$V_{BE(sat)(2)}$	$I_C = -500mA$ $I_B = -50mA$			-1.3	V
Transition Frequency	f_T	$V_{CE} = -10V$ $I_C = -20mA$ $f = 100MHz$	200			MHz
Delay Time	t_d	$V_{CC} = -30V$ $I_C = -150mA$ $I_{B1} = -15mA$			15	ns
Rise Time	t_r				20	ns
Storage Time	t_s	$V_{CC} = -30V$ $I_C = -150mA$ $I_{B1} = I_{B2} = -15mA$			225	ns
Fall Time	t_f				30	ns

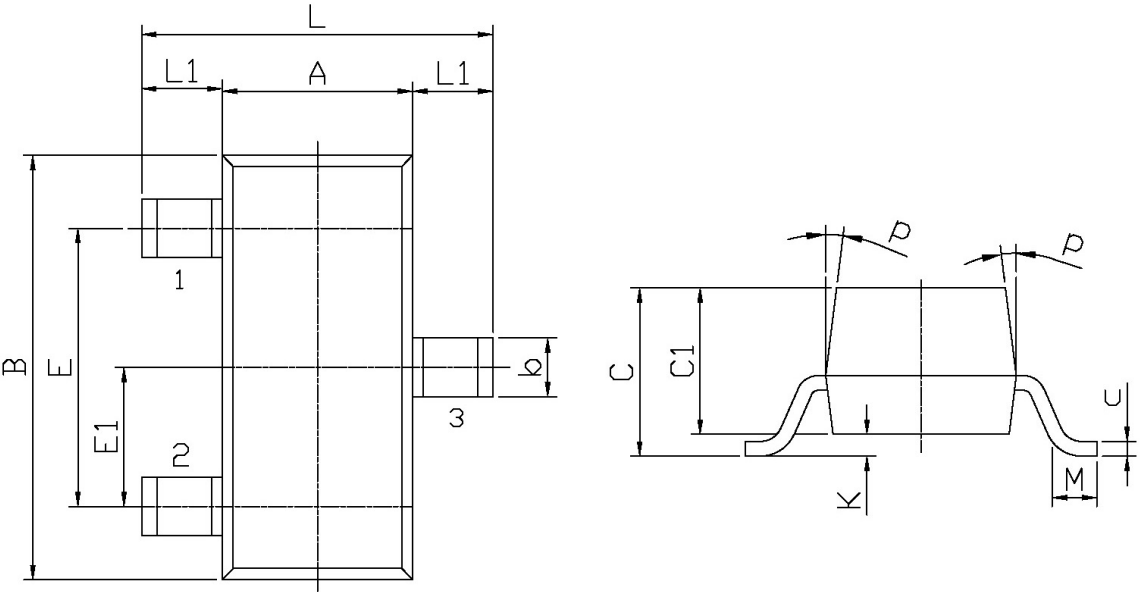
电参数曲线图 / Electrical Characteristic Curve



外形尺寸图 / Package Dimensions

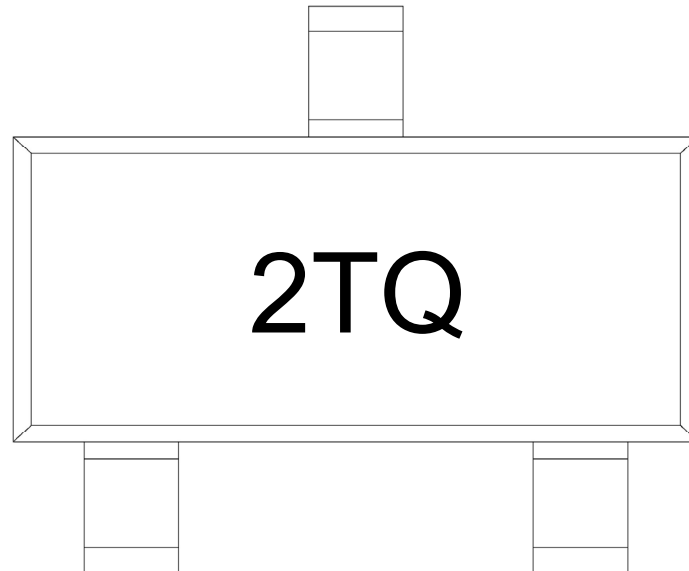
SOT-23

单位：mm



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
L	2.2	2.7	C	1.30Max	
L1	0.45	0.65	C1	0.90	1.20
A	1.15	1.50	c	0.05	0.20
B	2.70	3.10	K	0	0.10
E	1.70	2.10	M	0.20MIN	
E1	0.85	1.05	P	7°	
b	0.35	0.55			

印章说明 / Marking Instructions



说明：

2T： 为型号代码

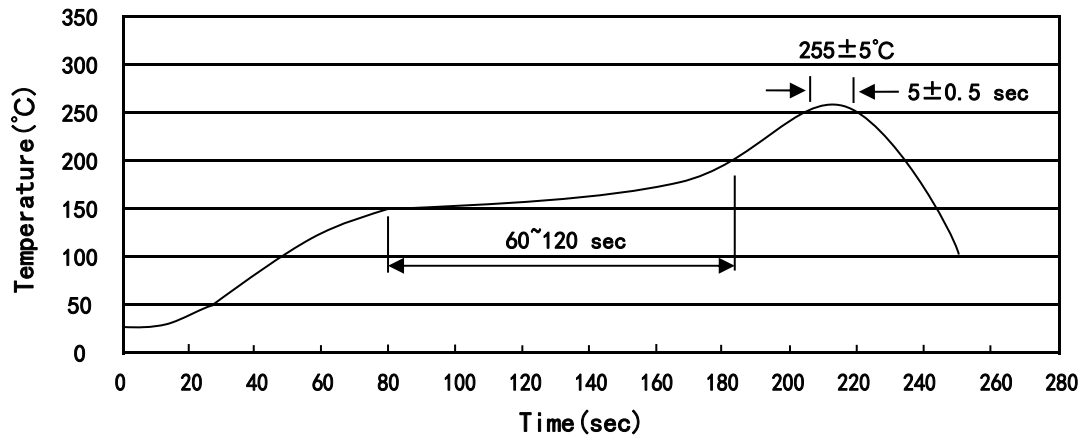
Q： 为汽车无卤产品标识

Note:

2T： Product Type Code

Q: Automobile halogen-free product Code

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)



说明：

- 1、预热温度 150 ~ 200°C，时间 60 ~ 120sec;
- 2、峰值温度 255±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2 ~ 10°C/sec.

Note:

- 1.Preheating:150~200°C, Time:60~120sec.
- 2.Peak Temp.:255±5°C, Duration:5±0.5sec.
- 3.Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-23	3,000	10	30,000	6	180,000	7" × 8	180×120×180	390×385×205

使用说明 / Notices